

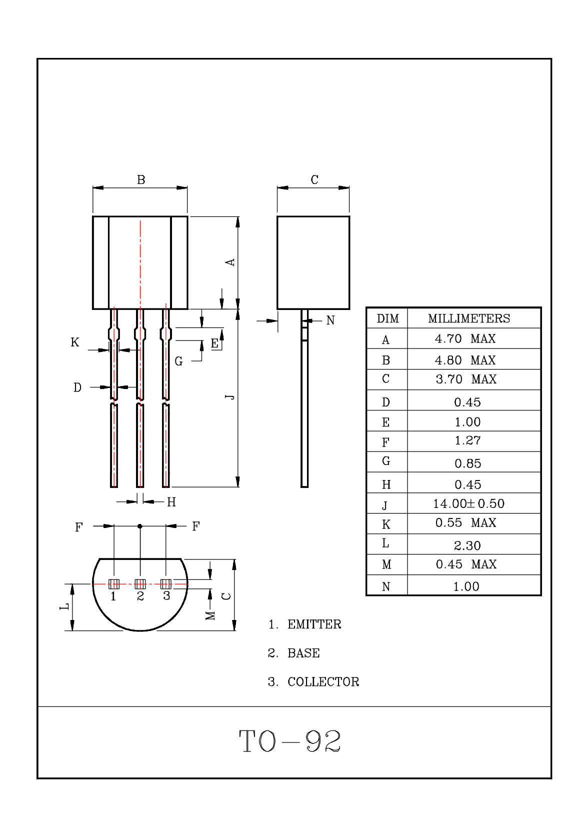
SEMICONDUCTOR
TECHNICAL DATA

KTC9012
EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURES

- Excellent h_{FE} Linearity.
- Complementary to KTC9013.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00± 0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Emitter Current	I_E	500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-35V, I_E=0	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-0.1	μA
DC Current Gain	h_{FE}(Note)	V_{CE}=-1V, I_C=-50mA	64	-	246	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA	-	-0.1	-0.25	V
Base-Emitter Voltage	V_{BE}	I_C=-100mA, V_{CE}=-1V	-	-0.8	-1.0	V
Transition Frequency	f_T	V_{CB}=-6V, I_C=-20mA, f=100MHz	150	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-6V, I_E=0, f=1MHz	-	7.0	-	pF

Note : h_{FE} Classification D:64～91, E:78～112, F:96～135,
G:118～166, H:144～202, I:176～246